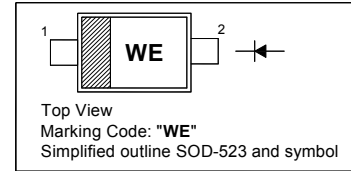


# 1PS70-02WT

## Silicon PIN Diode

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	50	V
Continuous Forward Current	$I_F$	100	mA
Total Power Dissipation ( $T_S = 90^\circ\text{C}$ )	$P_{tot}$	415	mW
Junction Temperature	$T_j$	- 65 to + 150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	$^\circ\text{C}$

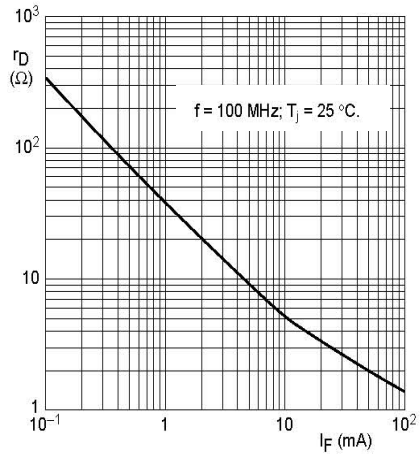
### Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 50\text{ mA}$	$V_F$	1.1	V
Reverse Current at $V_R = 50\text{ V}$	$I_R$	20	nA
Diode Capacitance at $V_R = 20\text{ V}$ , $f = 1\text{ MHz}$	$C_d$	0.25	pF
Forward Resistance at $I_F = 0.5\text{ mA}$ , $f = 100\text{ MHz}$ at $I_F = 1\text{ mA}$ , $f = 100\text{ MHz}$ at $I_F = 10\text{ mA}$ , $f = 100\text{ MHz}$ at $I_F = 100\text{ mA}$ , $f = 100\text{ MHz}$	$r_D$	100 50 7 1.9	$\Omega$

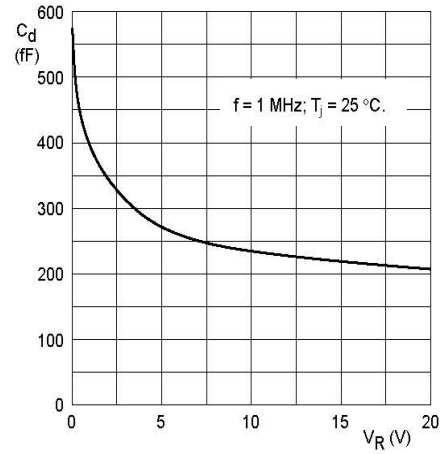
**TOP DYNAMIC**

# 1PS70-02WT

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Forward resistance as a function of forward current; typical values.



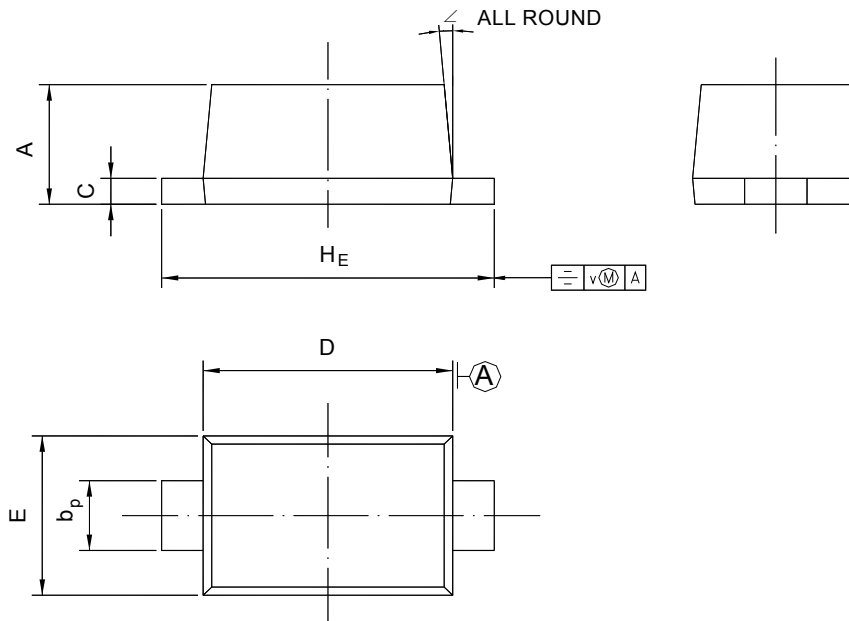
Diode capacitance as a function of reverse voltage; typical values.

# 1PS70-02WT

## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	$b_p$	C	D	E	$H_E$	V	$\angle$
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	$5^\circ$

**TOP DYNAMIC**